

**Cascadable Amplifier
1000 to 4000 MHz**

PA48 / SMPA48

V1

Features

- ULTRAWIDE BANDWIDTH: 0.8-4.2 GHz (TYP.)
- HIGH OUTPUT LEVEL: +24 dBm (TYP.)
- HIGH GAIN: 16.0 dB (TYP.)
- GaAs FET AMPLIFIER

Description

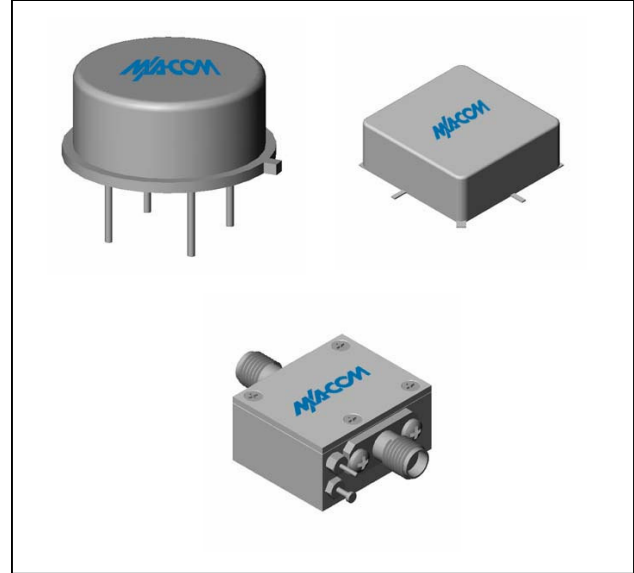
The PA48 power amplifier is a discrete hybrid design, which uses thin film manufacturing processes for accurate performance and high reliability. This two stage GaAs FET feedback amplifier design displays impressive performance characteristics over a broadband frequency range. Both TO-8 and Surface Mount packages are hermetically sealed, and MIL-STD-883 environmental screening is available.

Ordering Information

Part Number	Package
PA48	TO-8B
SMPA48	Surface Mount
CPA48 **	SMA Connectorized

** The connectorized version is not RoHS compliant.

Product Image



Electrical Specifications: $Z_0 = 50\Omega$, $V_{CC} = +15 V_{DC}$

Parameter	Units	Typical	Guaranteed	
		25°C	0° to 50°C	-54° to +85°C*
Frequency	GHz	0.8-4.2	1.0-4.0	1.0-4.0
Small Signal Gain (min)	dB	16.0	14.0	13.5
Gain Flatness (max)	dB	±0.4	±0.7	±0.8
Reverse Isolation	dB	33		
Noise Figure (max)	dB	5.5	7.0	7.5
Power Output @ 1 dB comp. (min)	dBm	24.0	22.5	21.5
IP3	dBm	+34		
IP2	dBm	+45		
Second Order Harmonic IP	dBm	+55		
VSWR Input / Output (max)		1.7:1 / 1.6:1	2.0:1 / 1.9:1	2.2:1 / 2.1:1
DC Current @ 15 Volts (max)	mA	225	235	245

Absolute Maximum Ratings

Parameter	Absolute Maximum
Storage Temperature	-62°C to +125°C
Case Temperature	+85°C
DC Voltage	+16 V
Continuous Input Power	+17 dBm
Short Term Input power (1 minute max.)	100 mW
Peak Power (3 µsec max.)	0.25 W
"S" Series Burn-In Temperature (case)	+85°C

Thermal Data: $V_{CC} = +15 V_{DC}$

Parameter	Rating
Thermal Resistance θ_{jc}	75°C/W
Transistor Power Dissipation P_d	1.264W
Junction Temperature Rise Above Case T_{jc}	+95°C

* Over temperature performance limits for part number CPA48, guaranteed from 0°C to +50°C only.

